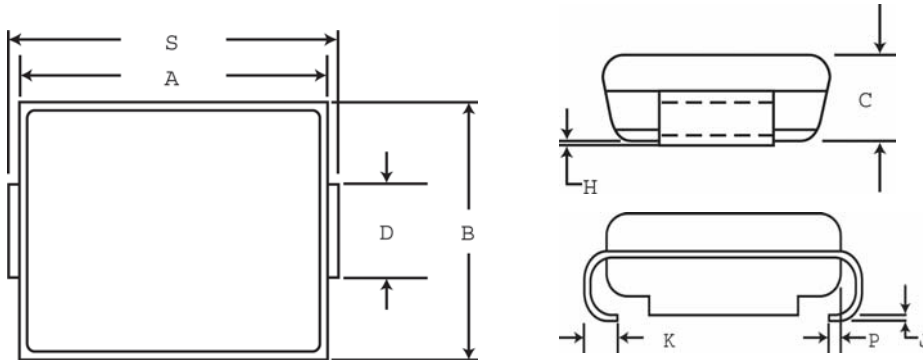
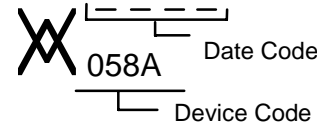


Specification Status: Released

PHYSICAL DESCRIPTION



Marking:



	A		B		C		D**		H		J		K	
mm:	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX
in*:	(0.160)	(0.180)	(0.130)	(0.155)	(0.075)	(0.096)	(0.077)	(0.086)	(0.002)	(0.008)	(0.006)	(0.012)	(0.030)	(0.060)

	P	S	
mm:	REF	MIN	MAX
in*:	(0.020)	(0.205)	(0.220)

*Rounded off approximation

** D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P

Other Physical Characteristics

- Form Factor: SMB (Surface Mount, JEDEC DO-214AA Package)
- Lead Material: Matte Tin finish
- Encapsulation Material: Epoxy, meets UL94 V-0 requirements
- Solderability: per MIL-STD-750, Method 2026
- Solder Heat Withstand: per MIL-STD-750, Method 2031
- Solvent Resistance: per MIL-STD-750, Method 1022
- Mechanical Shock: per MIL-STD-750, Method 2016
- Vibration: per MIL-STD-750, Method 2056

Tape and Reel packaging per EIA 481-1

- Agency Recognition: UL
- Precedence: This specification takes precedence over documents referenced herein.
- CAUTION: Operation beyond the rated voltage or current may result in rupture, electrical arcing or flame.

Materials Information

RoHS Compliant
Directive 2002/95/EC Compliant

ELV Compliant
Directive 2000/53/EC Compliant

OBSOLETE
NOT the LATEST REVISION

SiBar™ Thyristor Surge Protectors

Raychem Circuit Protection Products

Parameter	Symbol	Value	Units
Repetitive Off-State Voltage, Maximum at $I_D = 5 \mu A$	VDM	58	V
Non-Repetitive Peak Impulse Current	IPP ₁	50	A
Telcordia GR-1089 CORE 10x1000 μs			
Impulse Current	IPP ₂	70	A
TIA-968 lightning Type A Metallic 10/560 μs			
Double exponential Waveform	IPP ₃	90	A
TIA-968 lightning Type A Longit. 10/160 μs			
Telcordia GR-1089 Intrabuilding 2/10 μs	IPP ₄	150	A
(Notes 1 and 2)			
IEC61000-4-5 (Voc 1.2/50us) 8/20 μs	IPP ₅	150	A
ITU-T K.20/K.21 (Voc 10/700us) 5/310us	IPP ₆	80	A
TIA-968 lightning Type B (Voc 9/720us) 5/320 μs	IPP ₇	80	A
Critical Rate of Rise of On-State Current			
Power Pulse Amplifier, C=30 μF , V=600V	di/dt	500	A/ μs
Maximum 2x10 μs waveform, V _{OC} =750V, I _{SC} =150A peak	di/dt	100	A/ μs

DEVICE THERMAL RATINGS

Storage Temperature Range	TSTG	-55 to 150	°C
Operating Temperature Range Blocking or conducting state	TA	-40 to 125	°C
Overload Junction Temperature Maximum; Conducting state only	TJ	+150	°C
Maximum Lead Temperature for Soldering Purpose; for 10 seconds	TL	+260	°C

ELECTRICAL CHARACTERISTICS Both polarities (T_J @ 25°C unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	Units
Breakover Voltage (+25°C) (dv/dt = 0.4kV/ms, I _{SC} =900mA, V _{DC} = 500V (both polarities))	VBO	----	64	78	V
Breakover Voltage Temperature Coefficient	dVBO/dTJ	----	0.1	-----	%/°C
Off-State Current (VD1= 50V)	ID1	----	-----	2.0	μA
(VD2=VDM)	ID2=IDM	----	-----	5.0	μA
On-State Voltage (IT=1A) PW \leq 300 μs , Duty Cycle \leq 2% (Note 2)	VT	----	-----	4.0	V
Breakover Current	IBO	----	-----	800	mA
Holding Current (Note 2)	IH	150	----	-----	mA
Peak Onstage Surge Current (Measured @ 60Hz, 1 cycle, 600V)	ITSM	22	----	-----	A
Critical Rate of Rise of Off-State Voltage (Linear waveform, VD = 0.8 X Rated VBO, TJ= +25°C)	dv/dt	2000	----	-----	V/ μs
Capacitance (f=1.0 Mhz, 50Vdc bias, 1Vrms)	C1	----	43	-----	pF
(f=1.0 Mhz, 2Vdc bias, 1Vrms)	C2	----	80	-----	pF

Note 1. Allow cooling before testing second polarity

Note 2. Measured under pulse conditions to reduce heating

VOLTAGE-CURRENT CHARACTERISTIC

